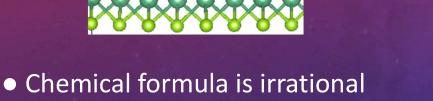
MISMATCHED INTERFACE THEORY (MINT)

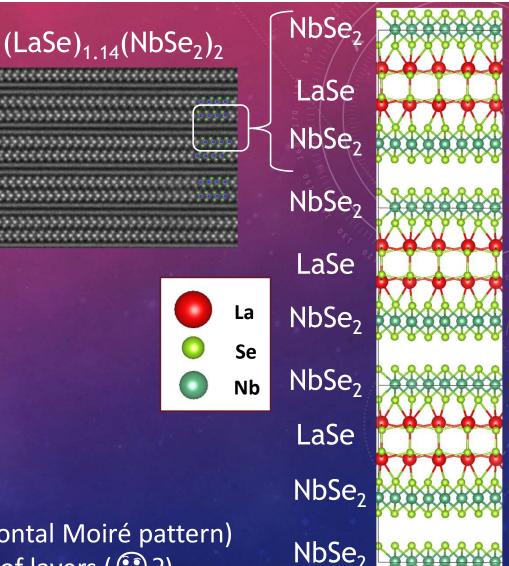
What to do when there is no good supercell?

Taken extensively from Niedzielski, Faeth, Goodge, Sinha, McQueen, Kourkoutis and Arias APS Bulletin: bit.ly/3Og42Tf

MISFIT MATERIALS (LaSe)_{1.14}(NbSe₂)₂

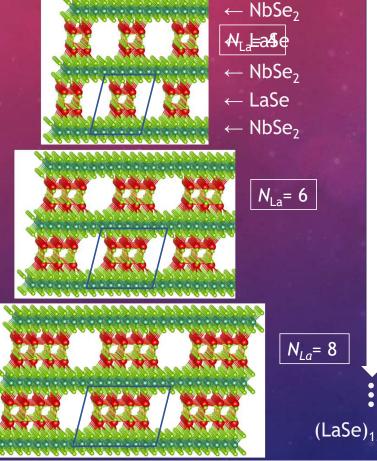


- Layers remain intact, no misfit dislocations
- Horizontal lattice constants mismatched
- There is no overall periodicity (forms horizontal Moiré pattern)
- Any supercell will strain one or both types of layers (?)



MINT-SANDWHICH

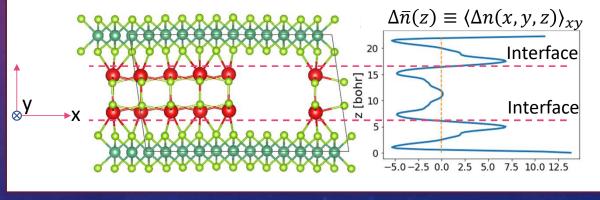
Sequence of periodic prototype materials (with voids)



Convergent sequence for desired material property

Charge transfer

Compute n(r) for combined and isolated systems
 Δn(r) ≡ n_{(LaSe)(NbSe₂)}(r) - n_{LaSe}(r) - n_{Nb₂}(r)
 ΔN ≡ ∫_{LaSe} n(r) d³r

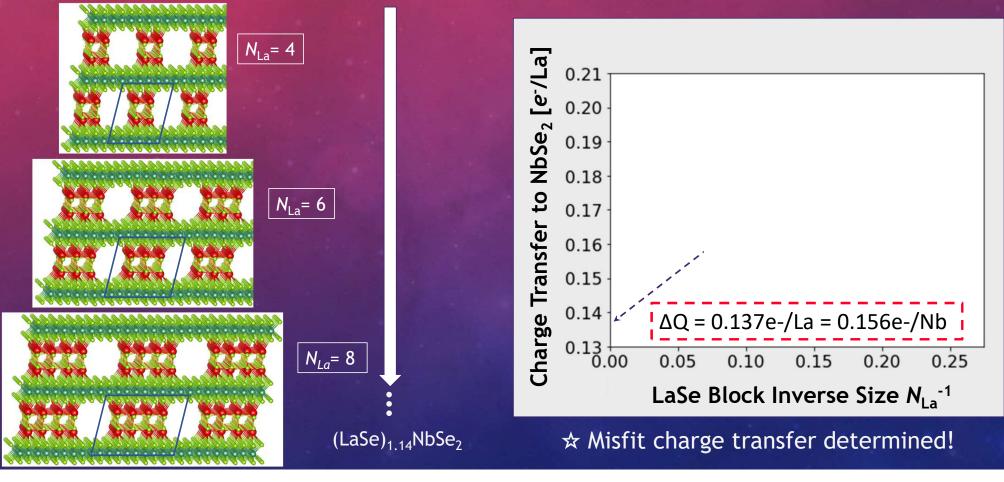


(LaSe)_{1.14}NbSe₂

MINT-SANDWICH

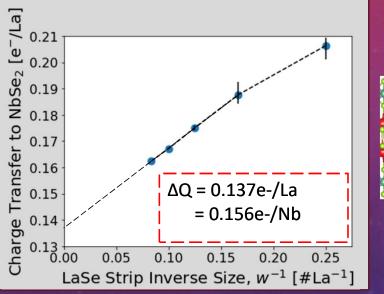
Sequence of periodic prototype materials (with voids)

Charge transfer



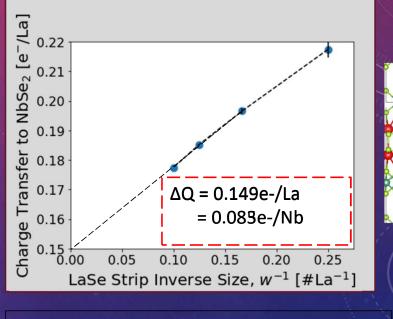
INTERLAYER CHARGE TRANSFER

LaSe NbSe₂





LaSe $(NbSe_2)_2$

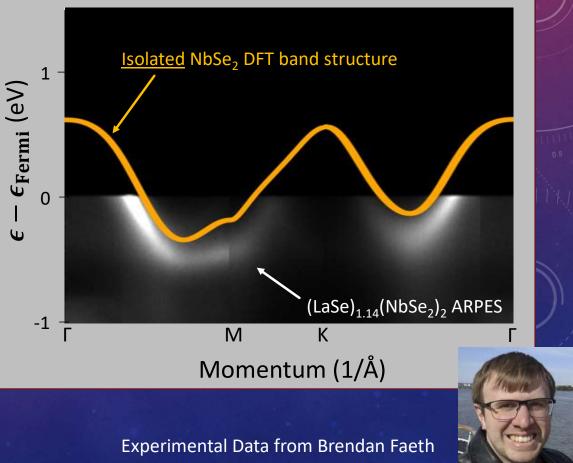


 \Rightarrow Compare to ARPES d-band shift!

ARPES CHARGE TRANSFER

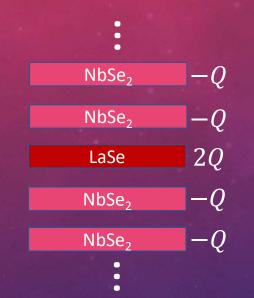
- ARPES measures filled states only
- Compute charge transfer from movement of Fermi level Nb-d band
- Luttinger Volume Analysis: $\Delta Q_{ARPES} = 0.51(5)e$ -/Nb
- Ab initio $\Delta Q_{MINT} = 0.082(6)e/Nb$ << ΔQ_{ARPES} ???
- Correct MINT electronic structure?

ARPES Experiment for (LaSe)_{1.14}(NbSe₂)₂



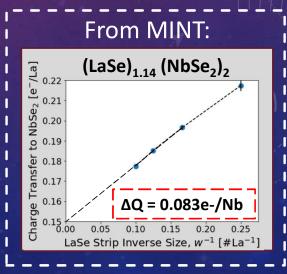
QUANTUM CAPACITOR MODEL:

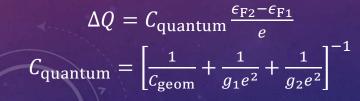
Capacitor Model



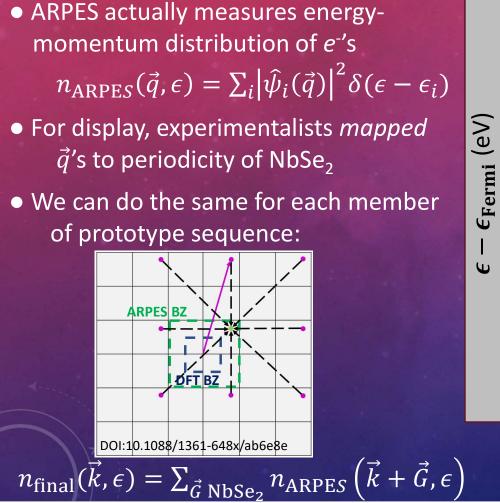
<u>Ab initio data</u>		
	g (eV-1/A)	$\epsilon_{ m F}$ (eV)
LaSe	0.102	-2.75
NbSe2	0.115	-5.54

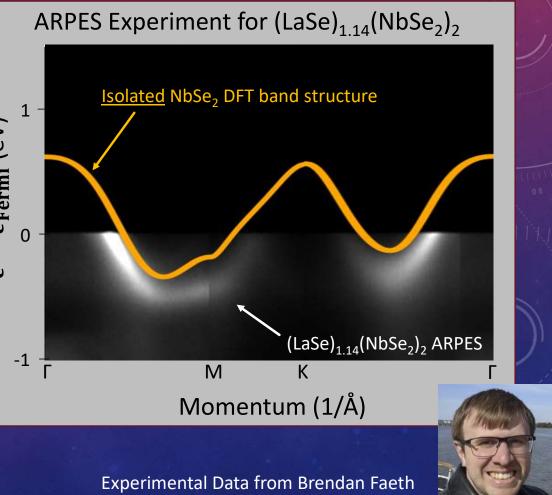
$$\Rightarrow dQ = 0.064 \text{ e-/Nb}$$



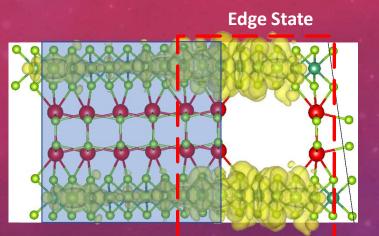


ARPES BAND-STRUCTURE WITHOUT PERIODICITY?





ACCELERATING CONVERGENCE



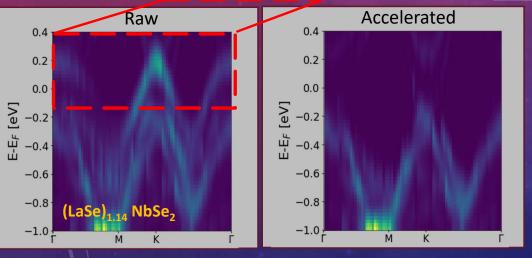
lssue

- Appearance of ghost band
- Become negligible as prototype grows, but undesirably slowly
- Cause: vacuum regions lead to <u>edge states</u>

Solution

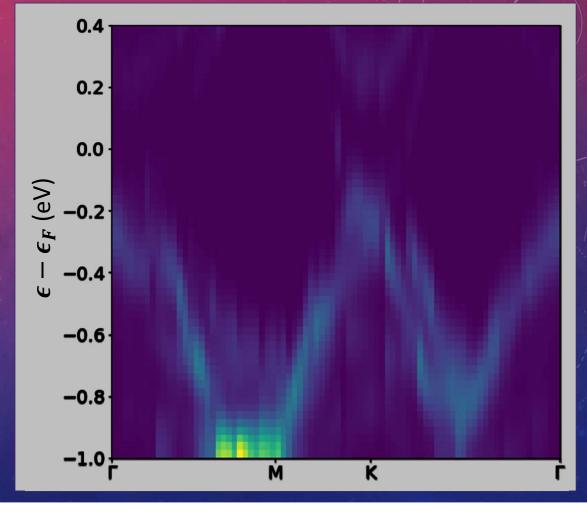
- Compute probablilty of each state in bulk region: $W_i \equiv \int_{\text{bulk}} |\psi_{n\vec{k}}(\vec{r})|^2 d^3r$
- Weigh each state accordingly:

$$n_{\text{ARPES}}(\vec{q},\epsilon) = \sum_{i} W_{i} |\hat{\psi}_{i}(\vec{q})|^{2} \delta(\epsilon - \epsilon_{i})$$



FIRST AB INITIO INCOMMENSURATE ARPES PREDICTIONS

Single layer material (LaSe)_{1.14}NbSe₂



RESULT FOR DOUBLE-LAYER MATERIAL

(LaSe)_{1.14}(NbSe₂)₂

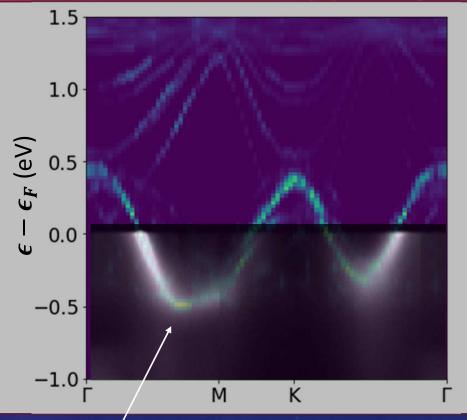
 Excellent Agreement (!!!) with ARPES measurements on (LaSe)_{1.14} (NbSe₂)₂.

 Fully consistent with ARPES result of 0.51(5)e-/Nb into Nb d-band

 However, our calculated interlayer charge transfer is 0.082(6)e-/Nb

Resolution is <u>pseudodoping!</u>

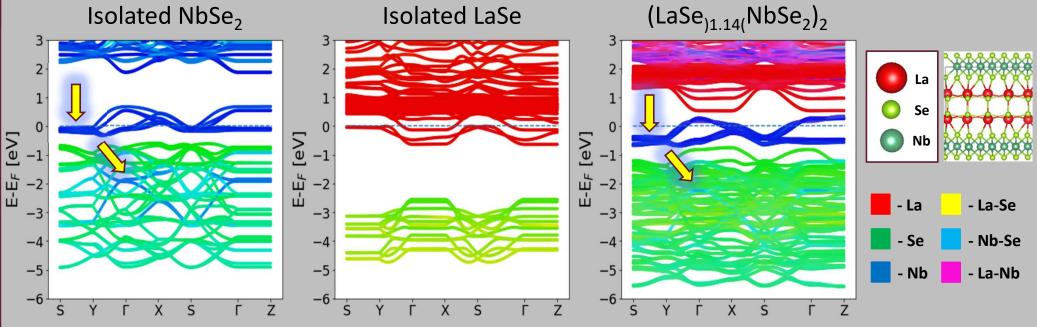




(LaSe)_{1.14} (NbSe₂)₂ measurement overlay

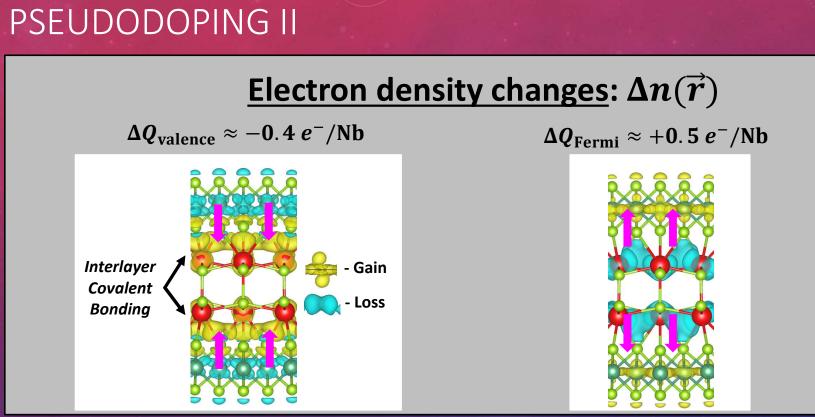
PSEUDODOPING I





• Nb d-bands (blue) drop below ϵ_F and gain electrons \checkmark

• Se p-bands (green/cyan, -3 eV $< \epsilon < -1$ eV) lose significant Nb character, Nb also loses e^{-1} 's ...



• Covalent bonding shifts $\approx -0.4 e^-/Nb$ away from valence Nb-d orbitals

- Charge imbalance nearly compensated by ≈ +0.5 e⁻/Nb gain in Femi-level Nb-d orbital (explains ARPES observation)
- Net gain in layer is $\approx +0.1 e^{-}/Nb$ (explains MINT charge transfer)

THANK YOU!

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